

Parameterization of Energy Bands and Optical Properties in Semiconductor $Culn_{1-x}Ga_xSe_2$

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Motivation

Parameterization of Energy Bands in $CuIn_{1-x}Ga_xSe_2$

Optical Properties of Culn_{0.5} Ga_{0.5} Se₂

Current Work



According to the statistical review of world energy on 2012.

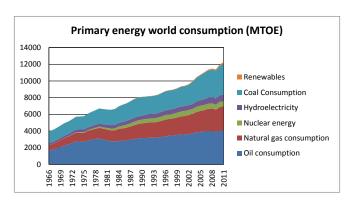


Figure 1: Figure is from BP statistical review of world energy 2012, METO means million tonnes oil equivalent.





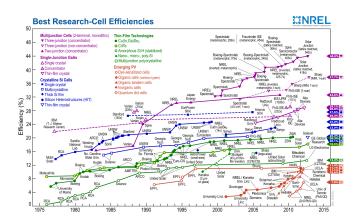


Figure 2: Best research-cell efficiencies. Figure is from National Renewable Energy Laboratory (NREL), Golden, Colorado.



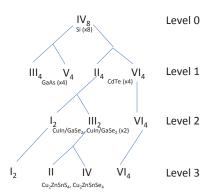


Figure 3: Candidate of solar cell materials (absorption coefficient, band gap range, cost and environmental safety).



By considering the electron energy dispersion only around the Γ -point (centre of the Brillouin zone), the parabolic band approximation (pba) is utilized:

$$E_j^{pb}(\mathbf{k}) = E_j(\mathbf{0}) \pm \left[\frac{\widetilde{\mathbf{k}}_x^2 + \widetilde{\mathbf{k}}_y^2}{m_j^{\perp}} + \frac{\widetilde{\mathbf{k}}_z^2}{m_j^{\parallel}} \right]$$
(1)

A common way to parameterize the energy bands is within the so called $K \cdot P$ approximation. However, the crystal-field interaction as well as the spin-orbit coupling of $Culn_{1-x}Ga_xSe_2$ generates rather complex energy dispersions. So we extend the $K \cdot P$ expressions to higher orders.



$$E_{j}(\mathbf{k}) = E_{j}^{pb}(\mathbf{k}) + E_{j}^{0} + \Delta_{j,1} \left(\delta_{j,1}^{2} \left(\frac{\widetilde{\mathbf{k}}_{x}^{4} + \widetilde{\mathbf{k}}_{y}^{4}}{m_{0}^{2}} \right) + \delta_{j,2}^{2} \left(\frac{\widetilde{\mathbf{k}}_{x}^{2} \widetilde{\mathbf{k}}_{y}^{2}}{m_{0}^{2}} \right) + 1 \right)^{1/2}$$

$$+ \Delta_{j,2} \left(\delta_{j,3}^{3} \left(\frac{\widetilde{\mathbf{k}}_{x}^{6} + \widetilde{\mathbf{k}}_{y}^{6}}{m_{0}^{3}} \right) + \delta_{j,4}^{3} \left(\frac{\widetilde{\mathbf{k}}_{x}^{2} \widetilde{\mathbf{k}}_{y}^{4} + \widetilde{\mathbf{k}}_{x}^{2} \widetilde{\mathbf{k}}_{y}^{2}}{m_{0}^{3}} \right) + 1 \right)^{1/3}$$

$$+ \Delta_{j,3} \left(\delta_{j,5}^{2} \left(\frac{\widetilde{\mathbf{k}}_{z}^{4}}{m_{0}^{2}} \right) + 1 \right)^{1/2} + \Delta_{j,4} \left(\delta_{j,6}^{3} \left(\frac{\widetilde{\mathbf{k}}_{z}^{6}}{m_{0}^{3}} \right) + 1 \right)^{1/3}$$

$$+ \Delta_{j,5} \left(\delta_{j,7}^{2} \left(\frac{\widetilde{\mathbf{k}}_{x}^{2} \widetilde{\mathbf{k}}_{z}^{2} + \widetilde{\mathbf{k}}_{y}^{2} \widetilde{\mathbf{k}}_{z}^{2}}{m_{0}^{3}} \right) + 1 \right)^{1/2}$$

$$+ \Delta_{j,6} \left(\delta_{j,8}^{3} \left(\frac{\widetilde{\mathbf{k}}_{x}^{4} \widetilde{\mathbf{k}}_{z}^{2} + \widetilde{\mathbf{k}}_{y}^{4} \widetilde{\mathbf{k}}_{z}^{2}}{m_{0}^{3}} \right) + \delta_{j,9}^{3} \left(\frac{\widetilde{\mathbf{k}}_{x}^{2} \widetilde{\mathbf{k}}_{z}^{4} + \widetilde{\mathbf{k}}_{y}^{2} \widetilde{\mathbf{k}}_{z}^{4}}{m_{0}^{3}} \right) + \delta_{j,10}^{3} \left(\frac{\widetilde{\mathbf{k}}_{x}^{2} \widetilde{\mathbf{k}}_{y}^{2} \widetilde{\mathbf{k}}_{z}^{2}}{m_{0}^{3}} \right) + 1 \right)^{1/3}$$

$$(2)$$



Unfortunately, the rather complex VB energy dispersions of $CuIn_{1-x}Ga_xSe_2$ require quite many fitting parameters. The CB, however, needs less parameters.

The lowest conduction band (CB) and the three uppermost valence bands (VBs) of $CuIn_{1-x}Ga_xSe_2$ (x=0, 0.5, and 1) in order to better describe of the non-parabolic and anisotropic.



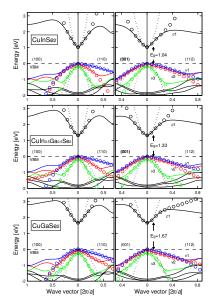


Figure 4: Electronic band structure along four directions. the circles are the results of the full band parameterization (fbp), and the dotted lines represent the parabolic band approximation.



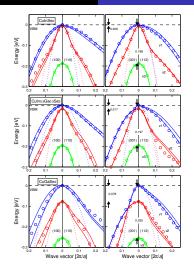


Figure 5: Close-up of above figure





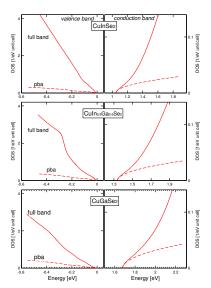


Figure 6: Total DOS $(g_{v/c}(E))$ of the VBs (left panels) and of the CB (right panels) for $Culn_{1-x}Ga_xSe_2$. The solid lines show the full band parameterization (fbp), and the dashed lines represent the parabolic band approximation (pba).



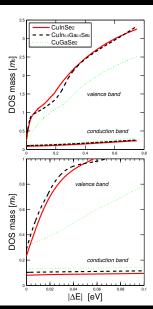


Figure 7: The DOS mass of the VBs and the CB in $CuIn_{1-x}Ga_xSe_2$. The upper (lower) panel shows in a wider (narrower) energy region.



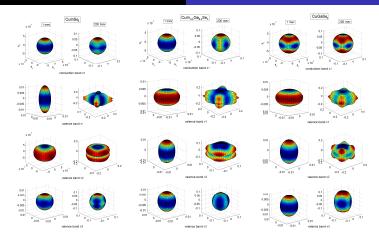


Figure 8: Constant energy surfaces for the three uppermost VBs and the lowest CB for the energies $\mathsf{E}=1$ meV (left column ellipsoidal) and $\mathsf{E}=200$ meV (right column).



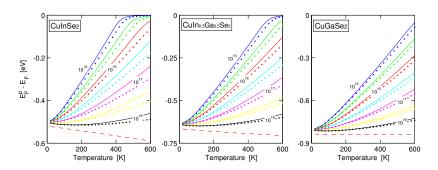


Figure 9: Fermi level as functon of the temperature fo p-type $CuIn_{1-x}Ga_xSe_2$ for the effective doping concentration $N_A=10^{13},10^{14},10^{15},...$, and 10^{19} acceptors/ cm^3 . Solid and dotted lines represent the full band parameterization and the parabolic band approximation, respectively.



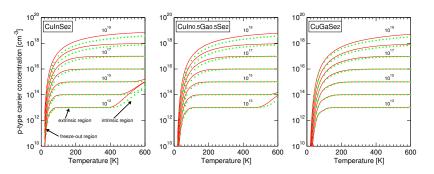


Figure 10: Free carrier concentration as function for the temperature in p-type for the effective doping concentration $N_A=10^{13},10^{14},10^{15},...$, and 10^{19} acceptors/ cm^3 . Solid and dotted lines represent the full band parameterization and the parabolic band approximation, respectively.



The dielectric function spectra of $CuIn_{0.5}Ga_{0.5}Se_2$ is calculated with full-potential linearized augmented plane wave method (Wien2k) using the generalized gradient approximation plus an onsite Coulomb interaction U of the Cu d states, it is compared with experiment as well. Probable electronic origins of the interband critical features (CPs) observed are discussed.



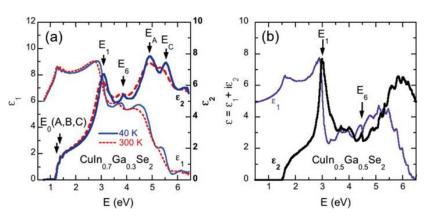


Figure 11: (a) Modeled dielectric function spectra for $Culn_{0.7}Ga_{0.3}Se_2$ taken at 40 K and 300 K. The dielectric function for $Culn_{0.5}Ga_{0.5}Se_2$ calculated by the FPLAPW using the GGA+U



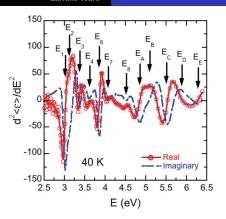


Figure 12: Solid red are standard CP lineshapes bet fit to $d^2 < \varepsilon_1 > /dE^2$ (open circles) and dashed-dotted blue lines are $d^2 < \varepsilon_2 > /dE^2$. Energies of each CP are indicated by arrows and labeled in a numeric and alphabetic order.



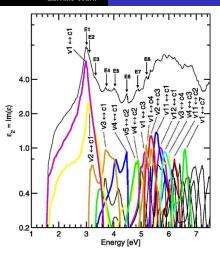


Figure 13: Band-to-band analysis of the contribution to the total ε_2 spectrum. The most important valence-to-conduction band transitions are marked. Spin-orbit coupling is included.



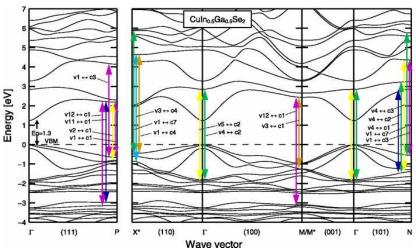


Figure 14: The calculated electronic band structure of $CuIn_{0.5}Ga_{0.5}Se_2$ where the CPs are identified along the main sysmetry directions.



I am involved in the implementation of the Exciting Code (Prof. Claudia DraxI), which is full-potential all-electron density-functional-theory (DFT) package implementing the families of linearized augmented planewave (LAPW) methods. The main work is about scalar relativistic approximation, spin-orbit coupling and new $K \cdot P$ method. Everything is under development now.

The code mainpage is http://exciting-code.org/, which has many features (TDDFT, GW and BSE ...).



Thank you for your time!